

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1.	6	((("6311888") or ("5985043") or ("6228680")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 14:54
S2	1017	(257/783).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:23
S3	2464	(257/778).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/01 17:38
S4	12	("5691103"   "5736681"   "5865934"   "5874780"   "5971253"   "6202915"   "6204089"   "6243946").PN. OR ("6311888").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/13 10:05
S5	12	("20010051392"   "5136365"   "5925930"   "6121689"   "6234379"   "6238948"   "6265776"   "6316286"   "6335571"   "6337265"   "6518677"   "6639321").PN. OR ("6815831").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/13 10:29
S6	19	(US-20030173683-\$ or US-20030001283-\$ or US-20020171156-\$ or US-20040253803-\$ or US-20040222522-\$).did. or (US-6774497-\$ or US-6774493-\$ or US-6426566-\$ or US-6365840-\$ or US-6815831-\$ or US-6311888-\$ or US-5874780-\$ or US-6639321-\$ or US-6518677-\$ or US-6335571-\$ or US-5925930-\$ or US-5691103-\$ or US-6204089-\$ or US-6228680-\$).did.	US-PGPUB; USPAT	OR	ON	2005/06/13 13:01
S7	186	third near (resin or underfill) near layer	US-PGPUB; USPAT	OR	ON	2005/06/13 13:02
S8	110	third adj (resin or underfill) adj layer	US-PGPUB; USPAT	OR	ON	2005/06/13 13:30
S9	1139	"flip chip" and passivation and (insulat\$3 adj (film or layer))	US-PGPUB; USPAT	OR	ON	2005/06/13 13:31

S10	231	"flip chip" and passivation and (insulat\$3 adj (film or layer)) and resin and reflow	US-PGPUB; USPAT	OR	ON	2005/06/13 15:07
S11	2	("6121689").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 16:24
S12	0	("("adhesionstrength"oradhesiveness)with("siliconnitride"orsin")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 16:26
S13	167	("adhesion strength" or adhesiveness) with ("silicon nitride" or sin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 16:32
S14	1	J/m with ("silicon nitride" or sin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 10:06
S15	3	J/m\$5 with ("silicon nitride" or sin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 10:48
S16	2	("SiOC" near2 insulat\$3) and "flip chip"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 12:48
S17	5832	"insulating film" near3 ("silicon nitride" or polyimide or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 12:49
S18	1693	"insulating film" near ("silicon nitride" or polyimide or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 12:49

S19	1475	"insulating film" adj ("silicon nitride" or polyimide or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 12:50
S20	19	"insulating film" adj (benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 13:30
S21	301	"silicon dioxide" near organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 13:32
S22	119	"passivation layer" with electrode with (polyimide or bcb or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 13:35
S23	18	"passivation" with bump with (polyimide or bcb or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 13:47
S24	2	("6306680").PN. OR ("6617696").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/14 13:38
S25	123	"passivation" with bump with (polyimide or bcb or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 13:47

S26	27	(US-20020171156-\$ or US-20030001283-\$ or US-20030173683-\$ or US-20040222522-\$ or US-20040253803-\$).did. or (US-5691103-\$ or US-5874780-\$ or US-5903058-\$ or US-5925930-\$ or US-6121689-\$ or US-6204089-\$ or US-6214446-\$ or US-6228680-\$ or US-6249044-\$ or US-6311888-\$ or US-6335571-\$ or US-6365840-\$ or US-6426566-\$ or US-6518677-\$ or US-6566234-\$ or US-6617696-\$ or US-6639321-\$ or US-6667230-\$ or US-6774493-\$ or US-6774497-\$ or US-6815831-\$).did. or (US-6586323-\$).did.	US-PGPUB; USPAT; DERWENT	OR	ON	2005/12/01 16:38
S27	2	("6077726").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/01 16:38
S28	6	("4048438"   "5744382").PN. OR ("6077726").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/01 16:45
S29	10	("20020086520"   "5137845"   "5554940"   "5756370"   "6077726"   "6162652"   "6194309"   "6197613"   "6406967"   "6426556").PN. OR ("6815324").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/01 17:10
S30	4	(S27 or S28 or S29) and constant	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/01 17:16
S31	1796	(257/738).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/01 17:22
S32	26	S31 and ("dielectric layer") and "dielectric constant"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:30
S33	2077	(257/737).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/01 17:22

S34	25	S33 and ("dielectric layer") and "dielectric constant"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:34
S35	84	S31 and "dielectric constant"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:30
S36	95	S33 and "dielectric constant"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:34
S37	2654	(257/778).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/01 17:38
S38	152	S37 and "dielectric constant"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:39
S39	152	S37 and "dielectric constant"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:48
S40	7822	("silicon dioxide" or "silicon oxynitride" or parylene or polyimide or "spin-on-glass" or sog) with "dielectric constant"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:50
S41	4941	S40 and "257"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:51

S42	3043	S40 and "257"/\$.ccls. and "dielectric layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:52
S43	0	"257"/\$.ccls. and "dielectric layer" and (("silicon dioxide" or "silicon oxynitride" or parylene or polyimide or "spin-on-glass" or sog) with "dielectric constant" with "less than")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:52
S44	0	((("silicon dioxide" or "silicon oxynitride" or parylene or polyimide or "spin-on-glass" or sog) with "dielectric constant" with "less than")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:53
S45	0	((("silicon dioxide" or "silicon oxynitride" or parylene or polyimide or "spin-on-glass" or sog) with "dielectric constant" and "less than")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:53